# **AN78MxxNSP Series**

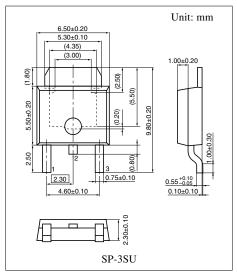
# 3-pin positive output voltage regulator (500 mA type)

#### ■ Overview

The AN78MxxNSP series is a 3-pin fixed positive output type monolithic voltage regulator housed in surface mounting package. Stabilized fixed output voltage is obtained from unstable DC input voltage with using minimum external components. 9 types of fixed output voltage are available; 5 V, 6 V, 7 V, 8 V, 9 V, 10 V, 12 V, 15 V and 18 V. They can be used widely in power circuits with current capacity up to 500 mA.

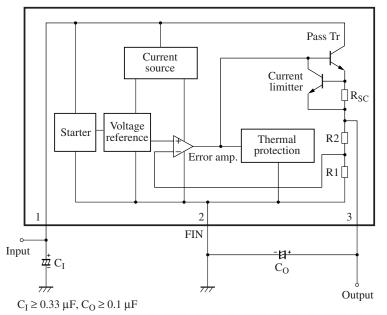
#### ■ Features

- Output voltage: 5V,6V,7V,8V,9V,10V,12V,15V,18 V
- Built-in overcurrent limit circuit
- Built-in thermal overload protection circuit
- Built-in ASO (area of safe operation) protection circuit



Note) The package of this product will be changed to lead-free type (SP-3SUA). See the new package dimensions section later of this datasheet.

## ■ Block Diagram



### ■ Pin Descriptions

Pin No.		Description				
1	Input	Input voltage pin				
2	GND	Ground pin (FIN)				
3	Output	Output voltage pin				

## ■ Absolute Maximum Ratings

Parameter	Symbol	Range	Unit
Supply voltage *2	V <sub>CC</sub>	35	V
Supply current *3	$I_{CC}$	_	mA
Power dissipation *4	$P_{\mathrm{D}}$	<del></del>	mW
Operating ambient temperature *1	T <sub>opr</sub>	-30 to +85	°C
Storage temperature *1	$T_{stg}$	-55 to +150	°C

Note) 1. \*1: Except for the operating ambient temperature and storage temperature, all ratings are for T<sub>a</sub> = 25°C.

- \*2: When  $V_{CC}$  of 35 V is applied, the overvoltage protection of ASO protection circuit may shut off the output.
- \*3: Since this IC has incorporated a current limiter, the current value does not exceed the rating.
- \*4: When Tj exceeds 150°C (designed value), the internal circuit cuts off the output. Note that the relationship between IC power dissipation and the ambient temperature must follow the derating curve.
- 2. This IC is not suitable for car electronics equipment.

## ■ Electrical Characteristics at T<sub>a</sub> = 25°C

#### • AN78M05NSP (5 V type)

The specified condition  $T_j = 25$  °C means that the test should be carried out within so short a test time (within 10 ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Unless otherwise specified,  $V_I$  = 10 V,  $I_O$  = 350 mA,  $C_I$  = 0.33  $\mu F$  and  $C_O$  = 0.1  $\mu F$ 

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V <sub>O1</sub>	$T_j = 25$ °C	4.8	5	5.2	V
Output voltage tolerance	V <sub>O2</sub>	$V_I$ = 7.5 V to 20 V, $I_O$ = 5 mA to 350 mA $T_j$ = 25°C	4.75	_	5.25	V
Line regulation 1	REG <sub>IN1</sub>	$V_I = 7.5 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	3	100	mV
Line regulation 2	REG <sub>IN2</sub>	$V_I = 8 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	1	50	mV
Load regulation 1	REG <sub>L1</sub>	$I_{O} = 5 \text{ mA to } 500 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	20	100	mV
Load regulation 2	REG <sub>L2</sub>	$I_{O} = 5 \text{ mA to } 200 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	10	50	mV
Bias current	I <sub>Bias</sub>	$T_j = 25$ °C	_	4	6	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = 8 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	_	0.8	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_O = 5 \text{ mA to } 350 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	_	0.5	mA
Ripple rejection ratio	RR	$V_I = 8 \text{ V to } 18 \text{ V}, I_O = 100 \text{ mA}, f = 120 \text{ Hz}$	62	_	_	dB

## · Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output noise voltage	V <sub>NO</sub>	f = 10  Hz to  100  kHz	_	40	_	μV
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$I_O = 500 \text{ mA}, T_j = 25^{\circ}\text{C}$		2		V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = 35 \text{ V}, T_j = 25^{\circ}\text{C}$	_	300	_	mA
Peak output current	I <sub>O(Peak)</sub>	$T_j = 25^{\circ}C$	_	1 000	_	mA
Output voltage temperature coefficient	$\Delta V_{\rm O}$ / $T_{\rm a}$	$I_O = 5 \text{ mA}, T_j = 0^{\circ}\text{C to } 125^{\circ}\text{C}$		- 0.5		mV/°C
Thermal protection operating temperature	$T_{j(TH)}$	$I_O = 5 \text{ mA}$		150		°C

## • AN78M06NSP (6 V type)

The specified condition  $T_j = 25$ °C means that the test should be carried out within so short a test time (within 10 ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Unless otherwise specified,  $V_I$  = 11 V,  $I_O$  = 350 mA,  $C_I$  = 0.33  $\mu F$  and  $C_O$  = 0.1  $\mu F$ 

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V <sub>O1</sub>	$T_j = 25^{\circ}C$	5.75	6	6.25	V
Output voltage tolerance	V <sub>O2</sub>	$V_I = 8.5 \text{ V to } 21 \text{ V}, I_O = 5 \text{ mA to } 350 \text{ mA}$ $T_j = 25^{\circ}\text{C}$	5.7	_	6.3	V
Line regulation 1	REG <sub>IN1</sub>	$V_I = 8.5 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	5	100	mV
Line regulation 2	REG <sub>IN2</sub>	$V_I = 9 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	1.5	50	mV
Load regulation 1	REG <sub>L1</sub>	$I_O = 5 \text{ mA to } 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	20	120	mV
Load regulation 2	REG <sub>L2</sub>	$I_O = 5 \text{ mA to } 200 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	10	60	mV
Bias current	$I_{Bias}$	$T_j = 25^{\circ}C$	_	4	6	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = 9 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	_	0.8	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_O = 5 \text{ mA to } 350 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	_	0.5	mA
Ripple rejection ratio	RR	$V_I = 9 \text{ V to } 19 \text{ V}, I_O = 100 \text{ mA}, f = 120 \text{ Hz}$	59	_	_	dB

#### Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output noise voltage	V <sub>NO</sub>	f = 10  Hz to  100  kHz	_	45	_	μV
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$I_O = 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	2	_	V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = 35 \text{ V}, T_j = 25^{\circ}\text{C}$	_	300	_	mA
Peak output current	I <sub>O(Peak)</sub>	$T_j = 25^{\circ}C$	_	1 000	_	mA
Output voltage temperature coefficient	$\Delta V_{\rm O}$ / $T_{\rm a}$	$I_O = 5 \text{ mA}, T_j = 0^{\circ}\text{C to } 125^{\circ}\text{C}$	_	- 0.5	_	mV/°C
Thermal protection operating temperature	T <sub>j(TH)</sub>	$I_O = 5 \text{ mA}$	_	150	_	°C

## • AN78M07NSP (7 V type)

The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10 ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Unless otherwise specified,  $V_I$  = 12 V,  $I_O$  = 350 mA,  $C_I$  = 0.33  $\mu F$  and  $C_O$  = 0.1  $\mu F$ 

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V <sub>O1</sub>	$T_j = 25$ °C	6.7	7	7.3	V
Output voltage tolerance	V <sub>O2</sub>	$V_I = 9.5 \text{ V to } 22 \text{ V}, I_O = 5 \text{ mA to } 350 \text{ mA}$ $T_i = 25^{\circ}\text{C}$	6.65	_	7.35	V
Line regulation 1	REG <sub>IN1</sub>	$V_I = 9.5 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	6	100	mV
Line regulation 2	REG <sub>IN2</sub>	$V_I = 10 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	2	50	mV
Load regulation 1	REG <sub>L1</sub>	$I_O = 5 \text{ mA to } 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	20	140	mV
Load regulation 2	REG <sub>L2</sub>	$I_O = 5 \text{ mA to } 200 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	10	70	mV
Bias current	I <sub>Bias</sub>	$T_j = 25$ °C	_	4	6	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = 10 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	_	0.8	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_O = 5 \text{ mA to } 350 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	_	0.5	mA
Ripple rejection ratio	RR	$V_I = 10 \text{ V to } 20 \text{ V}, I_O = 100 \text{ mA}, f = 120 \text{ Hz}$	57	_	_	dB

#### Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output noise voltage	V <sub>NO</sub>	f = 10  Hz to  100  kHz	_	48	_	μV
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$I_O = 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	2		V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = 35 \text{ V}, T_j = 25^{\circ}\text{C}$	_	300		mA
Peak output current	I <sub>O(Peak)</sub>	$T_j = 25^{\circ}C$	_	1000	_	mA
Output voltage temperature coefficient	$\Delta V_{\rm O}$ / $T_{\rm a}$	$I_O = 5 \text{ mA}, T_j = 0^{\circ}\text{C to } 125^{\circ}\text{C}$	_	- 0.5	_	mV/°C
Thermal protection operating temperature	$T_{j(TH)}$	$I_O = 5 \text{ mA}$	_	150		°C

## • AN78M08NSP (8 V type)

The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10 ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Unless otherwise specified,  $V_I$  = 14 V,  $I_O$  = 350 mA,  $C_I$  = 0.33  $\mu F$  and  $C_O$  = 0.1  $\mu F$ 

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V <sub>O1</sub>	$T_j = 25^{\circ}C$	7.7	8	8.3	V
Output voltage tolerance	V <sub>O2</sub>	$V_I = 10.5 \text{ V to } 22 \text{ V}, I_O = 5 \text{ mA to } 350 \text{ mA}$	7.6	_	8.4	V
		$T_j = 25^{\circ}C$				
Line regulation 1	REG <sub>IN1</sub>	$V_I = 10.5 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	6	100	mV
Line regulation 2	REG <sub>IN2</sub>	$V_I = 11 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	2	50	mV
Load regulation 1	REG <sub>L1</sub>	$I_O = 5 \text{ mA to } 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	25	160	mV
Load regulation 2	REG <sub>L2</sub>	$I_{O} = 5 \text{ mA to } 200 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	10	80	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$	_	4.1	6	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = 10.5 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_		0.8	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_{O} = 5 \text{ mA to } 350 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	_	0.5	mA
Ripple rejection ratio	RR	$V_I = 11.5 \text{ V to } 21.5 \text{ V}, I_O = 100 \text{ mA}, f = 120 \text{ Hz}$	56	_	_	dB

#### Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output noise voltage	V <sub>NO</sub>	f = 10  Hz to  100  kHz	_	48	_	μV
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$I_O = 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	2	_	V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = 35 \text{ V}, T_j = 25^{\circ}\text{C}$	_	300	_	mA
Peak output current	I <sub>O(Peak)</sub>	$T_j = 25^{\circ}C$	_	1 000	_	mA
Output voltage temperature coefficient	$\Delta V_{\rm O}$ / $T_{\rm a}$	$I_O = 5 \text{ mA}, T_j = 0^{\circ}\text{C to } 125^{\circ}\text{C}$	_	- 0.5		mV/°C
Thermal protection operating temperature	T <sub>j(TH)</sub>	$I_O = 5 \text{ mA}$	_	150	_	°C

## • AN78M09NSP (9 V type)

The specified condition  $T_j = 25$ °C means that the test should be carried out within so short a test time (within 10 ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Unless otherwise specified,  $V_I$  = 15 V,  $I_O$  = 350 mA,  $C_I$  = 0.33  $\mu F$  and  $C_O$  = 0.1  $\mu F$ 

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V <sub>O1</sub>	$T_j = 25^{\circ}C$	8.65	9	9.35	V
Output voltage tolerance	V <sub>O2</sub>	$V_I = 11.5 \text{ V to } 24 \text{ V}, I_O = 5 \text{ mA to } 350 \text{ mA}$ $T_j = 25^{\circ}\text{C}$	8.55	_	9.45	V
Line regulation 1	REG <sub>IN1</sub>	$V_I = 11.5 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	7	100	mV
Line regulation 2	REG <sub>IN2</sub>	$V_I = 12 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	2	50	mV
Load regulation 1	REG <sub>L1</sub>	$I_{O} = 5 \text{ mA to } 500 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	25	180	mV
Load regulation 2	REG <sub>L2</sub>	$I_{O} = 5 \text{ mA to } 200 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	10	90	mV
Bias current	$I_{Bias}$	$T_j = 25$ °C	_	4.1	6	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = 12 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	_	0.8	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_{O} = 5 \text{ mA to } 350 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	_	0.5	mA
Ripple rejection ratio	RR	$V_I = 12 \text{ V to } 22 \text{ V}, I_O = 100 \text{ mA}, f = 120 \text{ Hz}$	56	_	_	dB

#### Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output noise voltage	V <sub>NO</sub>	f = 10  Hz to  100  kHz	_	60	_	μV
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$I_O = 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	2	_	V
output short-circuit current	I <sub>O(Short)</sub>	$V_I = 35 \text{ V}, T_j = 25^{\circ}\text{C}$	_	300	_	mA
Peak output current	I <sub>O(Peak)</sub>	$T_j = 25^{\circ}C$	_	1 000	_	mA
Output voltage temperature coefficient	$\Delta V_{\rm O}$ / $T_{\rm a}$	$I_O = 5 \text{ mA}, T_j = 0^{\circ}\text{C to } 125^{\circ}\text{C}$	_	- 0.5	_	mV/°C
Thermal protection operating temperature	$T_{j(TH)}$	$I_O = 5 \text{ mA}$	_	150	_	°C

## • AN78M10NSP (10 V type)

The specified condition  $T_j = 25$ °C means that the test should be carried out within so short a test time (within 10 ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Unless otherwise specified,  $V_I$  = 16 V,  $I_O$  = 350 mA,  $C_I$  = 0.33  $\mu F$  and  $C_O$  = 0.1  $\mu F$ 

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V <sub>O1</sub>	$T_j = 25^{\circ}C$	9.6	10	10.4	V
Output voltage tolerance	V <sub>O2</sub>	$V_I = 12.5 \text{ V to } 25 \text{ V}, I_O = 5 \text{ mA to } 350 \text{ mA}$ $T_j = 25^{\circ}\text{C}$	9.5	_	10.5	V
Line regulation 1	REG <sub>IN1</sub>	$V_I = 12.5 \text{ V to } 30 \text{ V}, T_j = 25^{\circ}\text{C}$	_	7	100	mV
Line regulation 2	REG <sub>IN2</sub>	$V_I = 13 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	2	50	mV
Load regulation 1	REG <sub>L1</sub>	$I_O = 5 \text{ mA to } 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	25	200	mV
Load regulation 2	REG <sub>L2</sub>	$I_O = 5 \text{ mA to } 200 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	10	100	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$	_	4.1	6	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = 13 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	_	0.8	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_O = 5 \text{ mA to } 350 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	_	0.5	mA
Ripple rejection ratio	RR	$V_I = 13 \text{ V to } 23 \text{ V}, I_O = 100 \text{ mA}, f = 120 \text{ Hz}$	56	_	_	dB

## · Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output noise voltage	V <sub>NO</sub>	f = 10  Hz to  100  kHz	_	65	_	μV
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$I_O = 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	2		V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = 35 \text{ V}, T_j = 25^{\circ}\text{C}$	_	300		mA
Peak output current	I <sub>O(Peak)</sub>	$T_j = 25^{\circ}C$	_	1 000	_	mA
Output voltage temperature coefficient	$\Delta V_{\rm O}$ / $T_{\rm a}$	$I_O = 5 \text{ mA}, T_j = 0^{\circ}\text{C to } 125^{\circ}\text{C}$	_	- 0.5		mV/°C
Thermal protection operating temperature	$T_{j(TH)}$	$I_O = 5 \text{ mA}$	_	150	_	°C

## • AN78M12NSP (12 V type)

The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10 ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Unless otherwise specified,  $V_I$  = 19 V,  $I_O$  = 350 mA,  $C_I$  = 0.33  $\mu F$  and  $C_O$  = 0.1  $\mu F$ 

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V <sub>O1</sub>	$T_j = 25^{\circ}C$	11.5	12	12.5	V
Output voltage tolerance	V <sub>O2</sub>	$V_I = 14.5 \text{ V to } 27 \text{ V}, I_O = 5 \text{ mA to } 350 \text{ mA}$ $T_j = 25 ^{\circ}\text{C}$	11.4	_	12.6	V
Line regulation 1	REG <sub>IN1</sub>	$V_I = 14.5 \text{ V to } 30 \text{ V}, T_j = 25^{\circ}\text{C}$	_	8	100	mV
Line regulation 2	REG <sub>IN2</sub>	$V_I = 16 \text{ V to } 30 \text{ V}, T_j = 25^{\circ}\text{C}$	_	2	50	mV
Load regulation 1	REG <sub>L1</sub>	$I_{O} = 5 \text{ mA to } 500 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	25	240	mV
Load regulation 2	REG <sub>L2</sub>	$I_{O} = 5 \text{ mA to } 200 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	10	120	mV
Bias current	$I_{Bias}$	$T_j = 25^{\circ}C$	_	4.3	6	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = 14.5 \text{ V to } 30 \text{ V}, T_j = 25^{\circ}\text{C}$	_	_	0.8	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_{O} = 5 \text{ mA to } 350 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	_	0.5	mA
Ripple rejection ratio	RR	$V_I = 15 \text{ V to } 25 \text{ V}, I_O = 100 \text{ mA}, f = 120 \text{ Hz}$	55	_	_	dB

#### Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output noise voltage	V <sub>NO</sub>	f = 10  Hz to  100  kHz	_	75	_	μV
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$I_O = 500 \text{ mA}, T_j = 25^{\circ}\text{C}$		2		V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = 35 \text{ V}, T_j = 25^{\circ}\text{C}$	_	300	_	mA
Peak output current	I <sub>O(Peak)</sub>	$T_j = 25^{\circ}C$	_	1 000	_	mA
Output voltage temperature coefficient	$\Delta V_{\rm O}$ / $T_{\rm a}$	$I_O = 5 \text{ mA}, T_j = 0^{\circ}\text{C to } 125^{\circ}\text{C}$	_	- 0.5	_	mV/°C
Thermal protection operating temperature	$T_{j(TH)}$	$I_O = 5 \text{ mA}$	_	150		°C

## • AN78M15NSP (15 V type)

The specified condition  $T_j = 25$ °C means that the test should be carried out within so short a test time (within 10 ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Unless otherwise specified,  $V_I$  = 23 V,  $I_O$  = 350 mA,  $C_I$  = 0.33  $\mu F$  and  $C_O$  = 0.1  $\mu F$ 

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V <sub>O1</sub>	$T_j = 25^{\circ}C$	14.4	15	15.6	V
Output voltage tolerance	V <sub>O2</sub>	$V_I$ = 17.5 V to 30 V, $I_O$ = 5 mA to 350 mA $T_j$ = 25°C	14.25	_	15.75	V
Line regulation 1	REG <sub>IN1</sub>	$V_I = 17.5 \text{ V to } 30 \text{ V}, T_j = 25^{\circ}\text{C}$	_	10	100	mV
Line regulation 2	REG <sub>IN2</sub>	$V_I = 20 \text{ V to } 30 \text{ V}, T_j = 25^{\circ}\text{C}$	_	3	50	mV
Load regulation 1	REG <sub>L1</sub>	$I_{O} = 5 \text{ mA to } 500 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	25	300	mV
Load regulation 2	REG <sub>L2</sub>	$I_{O} = 5 \text{ mA to } 200 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	10	150	mV
Bias current	I <sub>Bias</sub>	$T_j = 25$ °C	_	4.3	6	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = 17.5 \text{ V to } 30 \text{ V}, T_j = 25^{\circ}\text{C}$	_	_	0.8	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_O = 5 \text{ mA to } 350 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	_	0.5	mA
Ripple rejection ratio	RR	$V_I = 18.5 \text{ V to } 28.5 \text{ V}, I_O = 100 \text{ mA}, f = 120 \text{ Hz}$	54	_	_	dB

#### · Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output noise voltage	V <sub>NO</sub>	f = 10  Hz to  100  kHz	_	90	_	μV
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$I_O = 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	2		V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = 35 \text{ V}, T_j = 25^{\circ}\text{C}$	_	300		mA
Peak output current	I <sub>O(Peak)</sub>	$T_j = 25^{\circ}C$		1 000		mA
Output voltage temperature coefficient	$\Delta V_{\rm O}$ / $T_{\rm a}$	$I_O = 5 \text{ mA}, T_j = 0^{\circ}\text{C to } 125^{\circ}\text{C}$	_	- 0.5	_	mV/°C
Thermal protection operating temperature	T <sub>j(TH)</sub>	$I_O = 5 \text{ mA}$	_	150		°C

## • AN78M18NSP (18 V type)

The specified condition  $T_j = 25$ °C means that the test should be carried out within so short a test time (within 10 ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Unless otherwise specified,  $V_I$  = 27 V,  $I_O$  = 350 mA,  $C_I$  = 0.33  $\mu F$  and  $C_O$  = 0.1  $\mu F$ 

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V <sub>O1</sub>	$T_j = 25$ °C	17.3	18	18.7	V
Output voltage tolerance	V <sub>O2</sub>	$V_I = 21 \text{ V to } 33 \text{ V}, I_O = 5 \text{ mA to } 350 \text{ mA}$ $T_j = 25^{\circ}\text{C}$	17.1	_	18.9	V
Line regulation 1	REG <sub>IN1</sub>	$V_I = 21 \text{ V to } 33 \text{ V}, T_j = 25^{\circ}\text{C}$	_	10	100	mV
Line regulation 2	REG <sub>IN2</sub>	$V_I = 22 \text{ V to } 33 \text{ V}, T_j = 25^{\circ}\text{C}$	_	5	50	mV
Load regulation 1	REG <sub>L1</sub>	$I_O = 5 \text{ mA to } 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	30	360	mV
Load regulation 2	REG <sub>L2</sub>	$I_O = 5 \text{ mA to } 200 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	10	180	mV
Bias current	$I_{Bias}$	$T_j = 25^{\circ}C$	_	4.4	6	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = 21 \text{ V to } 33 \text{ V}, T_j = 25^{\circ}\text{C}$	_	_	0.8	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_O = 5 \text{ mA to } 350 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	_	0.5	mA
Ripple rejection ratio	RR	$V_I = 22 \text{ V to } 32 \text{ V}, I_O = 100 \text{ mA}, f = 120 \text{ Hz}$	53	_	_	dB

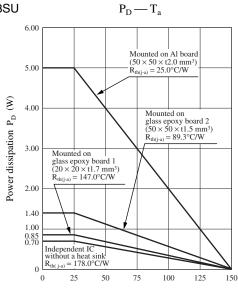
#### Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output noise voltage	V <sub>NO</sub>	f = 10  Hz to  100  kHz	_	100	_	μV
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$I_O = 500 \text{ mA}, T_j = 25^{\circ}\text{C}$		2		V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = 35 \text{ V}, T_j = 25^{\circ}\text{C}$	_	300	_	mA
Peak output current	I <sub>O(Peak)</sub>	$T_j = 25^{\circ}C$	_	1 000	_	mA
Output voltage temperature coefficient	$\Delta V_{\rm O}$ / $T_{\rm a}$	$I_O = 5 \text{ mA}, T_j = 0^{\circ}\text{C to } 125^{\circ}\text{C}$	_	- 0.5	_	mV/°C
Thermal protection operating temperature	$T_{j(TH)}$	$I_O = 5 \text{ mA}$	_	150		°C

## ■ Application Notes

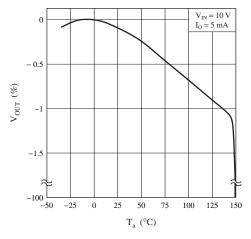
1. P<sub>D</sub> — T<sub>a</sub> curves of SP-3SU

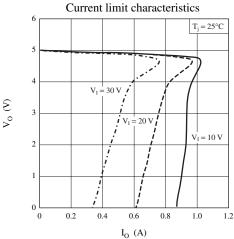


## Ambient temperature $T_a$ (°C)

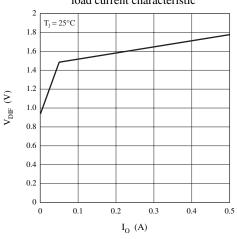
#### 2. Main Characteristics

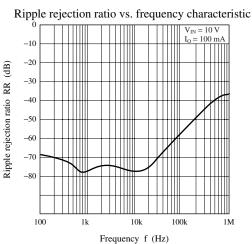
Output voltage temperature characteristic





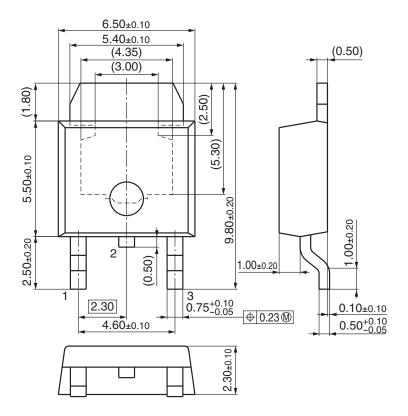
Minimum input/output voltage difference vs. load current characteristic





SFF00012BEB 11

- New Package Dimensions (Unit: mm)
- SP-3SUA (Lead-free package)



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